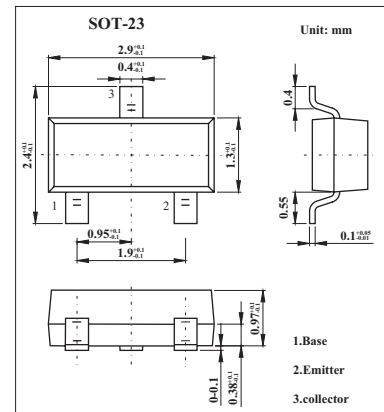


PNP General Purpose Transistors

BCW67,BCW68

■ Features

- For general AF applications.
- High current gain.
- Low collector-emitter saturation voltage.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	BCW67	BCW68	Unit
Collector-base voltage	V_{CB0}	-45	-60	V
Collector-emitter voltage	V_{CE0}	-32	-45	V
Emitter-base voltage	V_{EB0}	-5	-5	V
Collector current	I_C	-800		mA
Peak collector current	I_{CM}	-1000		mA
Base current	I_B	-100		mA
Peak base current	I_{BM}	-200		mA
Total power dissipation, $T_s = 79^\circ\text{C}$	P_{tot}	330		mW
Junction temperature	T_j	150		$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +150		$^\circ\text{C}$
Junction - soldering point	R_{thJS}	≤ 215		K/W

BCW67,BCW68

■ Electrical Characteristics Ta = 25°C

Parameter		Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	BCW67	V(BR)CEO	Ic = -10 mA, IB = 0	-32			V
	BCW68			-45			
Collector-base breakdown voltage	BCW67	V(BR)CBO	Ic = -10 μA, IE = 0	-45			V
	BCW68			-60			
Emitter-base breakdown voltage		V(BR)EBO	IE = -10μA, IC = 0	-5			V
Collector cutoff current	BCW67	ICBO	V _{CB} = -32 V, IE = 0			-20	nA
	BCW68		V _{CB} = -45 V, IE = 0			-20	
	BCW67	ICBO	V _{CB} = -32 V, IE = 0, TA = 150 °C			-20	μA
	BCW68		V _{CB} = -45 V, IE = 0, TA = 150 °C			-20	
Emitter cutoff current		IEBO	VEB = -4 V, IC = 0			-20	nA
DC current gain *	A/F	hFE	Ic = 100 μA, VCE = 10 V	35			
	B/G			50			
	C/H			80			
DC current gain *	A/F	hFE	Ic = 10 mA, VCE = 1 V	75			
	B/G			120			
	C/H			180			
DC current gain *	A/F	hFE	Ic = -100 mA, VCE = -1 V	100	160	250	
	B/G			160	250	400	
	C/H			250	350	630	
Collector-emitter saturation voltage *		VCE(sat)	Ic = -100 mA, IB = -10 mA			-0.3	V
			Ic = -500 mA, IB = -50 mA			-0.7	
Base-emitter saturation voltage *		VBE(sat)	Ic = -100 mA, IB = -10 mA			-1.25	
			Ic = -500 mA, IB = -50 mA			-2	
Transition frequency		fT	Ic = -50 mA, VCE = -5 V, f = 20 MHz		200		MHz
Collector-base capacitance		Ccb	V _{CB} = -10 V, f = 1 MHz		6		pF
Emitter-base capacitance		Ceb	VEB = -0.5 V, f = 1 MHz		60		

* Pulse test: t ≤ 300μs, D = 2%.

■ hFE Classification

TYPE	BCW67		
Rank	A	B	C
Marking	DAs	DBs	DCs

TYPE	BCW68		
Rank	F	G	H
Marking	DFs	DGs	DHs